

IGBT MODULE (F series)

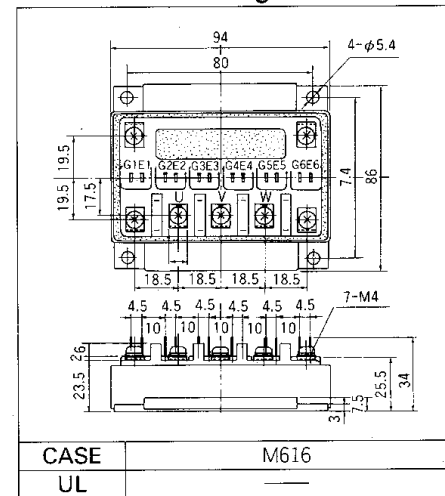
■ Features

- Low Saturation Voltage
- Voltage Drive
- Variety of Power Capacity Series

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings



■ Maximum Ratings and Characteristics

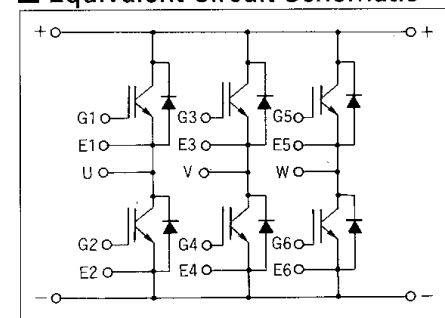
● Absolute Maximum Ratings

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V _{CE}	600	V
Gate-Emitter Voltage	V _{GE}	±20	V
Collector Current	Continuous	I _C	75
	1ms	I _{C pulse}	150
	Continuous	-I _C	75
	1ms	-I _{C pulse}	150
Max. Power Dissipation	P _C	290	W
Operating Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-40 to +125	°C
Net. Weight		510	g
Isolation Voltage	AC, 1min.	V _{isol}	2500
Screw Torque	Mounting *1	3.5 {35}	N · m
	Terminals *2	1.7 {17}	{kg · cm}

*1 Recommendable Value 2.5 to 3.5 N·m {25 to 35 kg·cm} (M5)

*2 Recommendable Value 1.3 to 1.7 N·m {13 to 17 kg·cm} (M4)

■ Equivalent Circuit Schematic

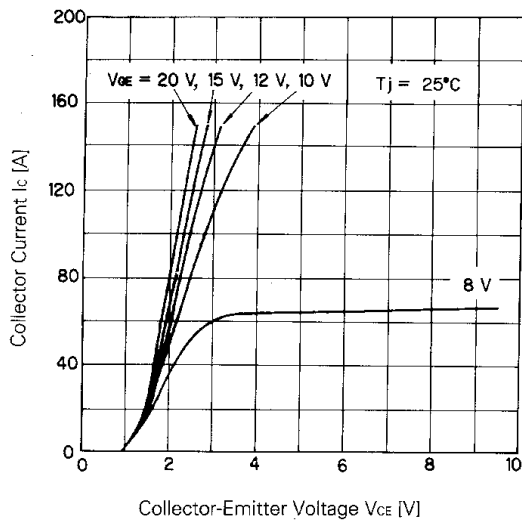


● Electrical Characteristics (T_c=25°C)

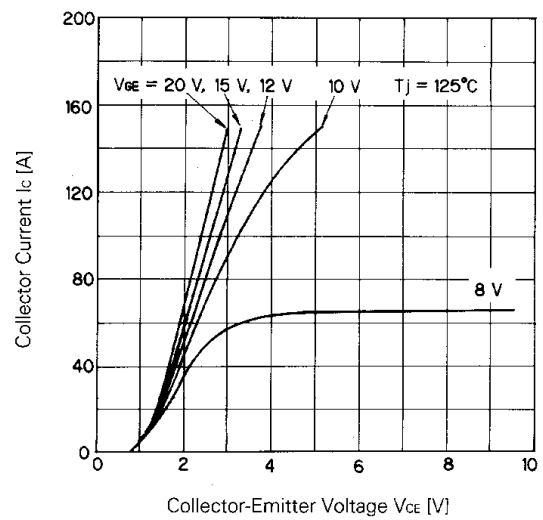
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CE}	V _{GE} =0V V _{CE} =600V T _J =25°C			1.0	mA
		V _{GE} =0V V _{CE} =600V T _J =125°C			—	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =±20V			100	nA
Gate-Emitter Threshold Voltage	V _{GE (th)}	V _{CE} =20V I _C =75mA	3.0		6.0	V
Collector-Emitter Saturation Voltage	V _{CE (sat)}	V _{GE} =15V I _C =75A			2.5	V
Input Capacitance	C _{ies}	V _{GE} =0V		7100		
Output Capacitance	C _{oes}	V _{CE} =10V		—		pF
Reverse Transfer Capacitance	C _{res}	f=1MHz		—		
Turn-on Time	t _{on}	V _{CC} =300V			0.8	μs
	t _r	I _C =75A			0.6	
Turn-off Time	t _{off}	V _{GE} =±15V			1.5	
	t _f	R _G =33Ω			1.0	
Diode Forward On-Voltage	V _F	I _F =75A, V _{GE} =0V			2.5	V
Reverse Recovery Time	t _{rr}	I _F =75A, -di/dt=250A/μs V _{GE} =-10V			300	ns

● Thermal Characteristics

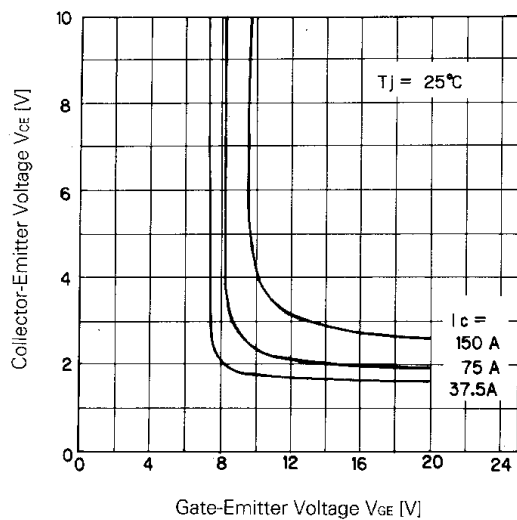
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th (j-cl)}	IGBT			0.431	°C/W
	R _{th (j-cl)}	Diode			0.888	
	R _{th (c-f)}	With Thermal compound		0.05		



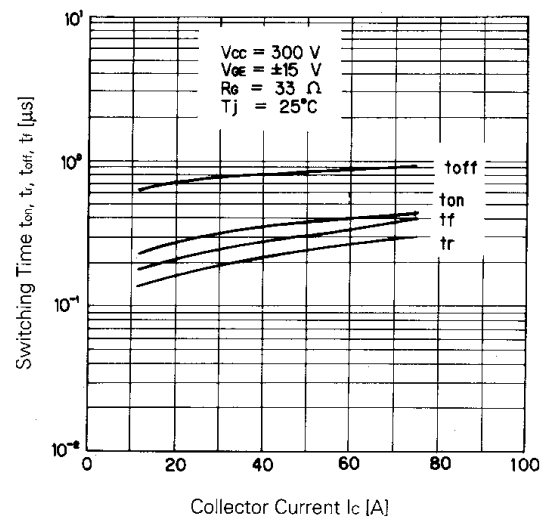
Collector Current vs. Collector-Emitter Voltage



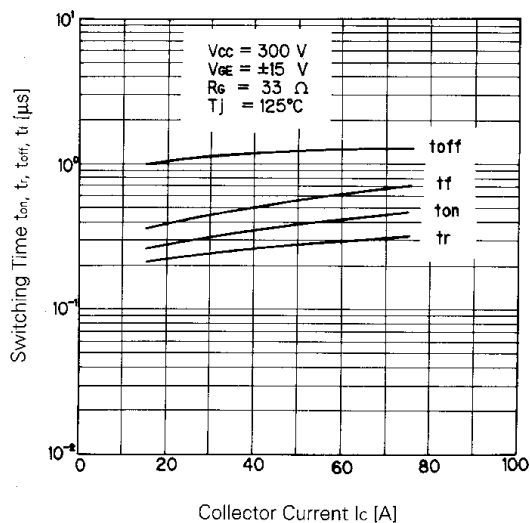
Collector Current vs. Collector-Emitter Voltage



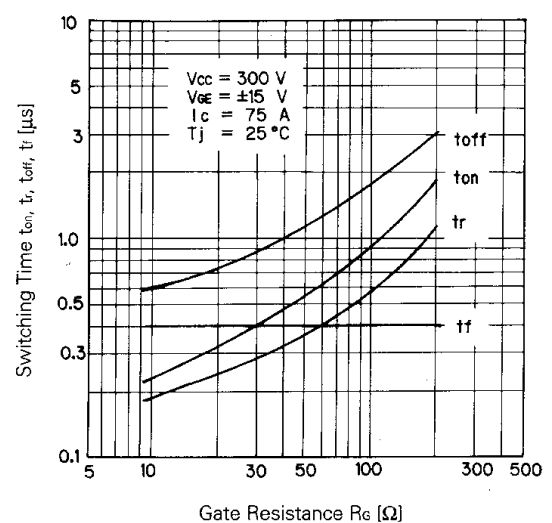
Collector-Emitter Voltage vs. Gate-Emitter Voltage



Switching Time



Switching Time



Switching Time-Gate Resistance

